RENESAS

H5N5004PL

Silicon N Channel MOS FET
High Speed Power Switching

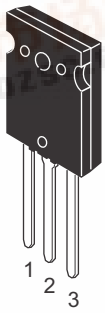
REJ03G1113-0200
(Previous: ADE-208-1381)
Rev.2.00
Sep 07, 2005

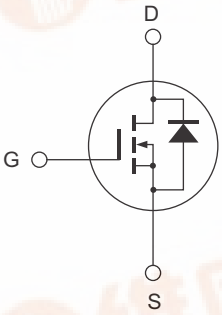
Features

- Low on-resistance: $R_{DS(on)}$ = 0.09 Ω typ.
- Low leakage current: I_{DSS} = 10 µA max (at V_{DS} = 500 V)
- High speed switching: t_f = 280 ns typ (at V_{GS} = 10 V, V_{DD} = 250 V, I_D = 25 A)
- Low gate charge: Qg = 220 nC typ (at V_{DD} = 400 V, V_{GS} = 10 V, I_D = 50 A)
- Avalanche ratings
- Built-in fast recovery diode: trr = 190 ns typ

Outline

RENESAS Package code: PRSS0004ZF-A
(Package name: TO-3PL)





1. Gate
2. Drain (Flange)
3. Source

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	V_{DSS}	500	V
Gate to source voltage	V_{GSS}	±30	V
Drain current	I_D	50	A
Drain peak current	$I_{D\ (pulse)}$ Note 1	200	A
Body-drain diode reverse drain current	I_{DR}	50	A
Body-drain diode reverse drain peak current	$I_{DR\ (pulse)}$ Note 1	200	A
Avalanche current	I_{AP} Note 3	15	A
Channel dissipation	Pch Note 2	250	W
Channel to case thermal Impedance	θ ch-c	0.5	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	–55 to +150	°C

Notes: 1. PW ≤ 10 µs, duty cycle ≤ 1%
2. Value at Tc = 25°C
3. Tch ≤ 150°C

Electrical Characteristics

(Ta = 25°C)

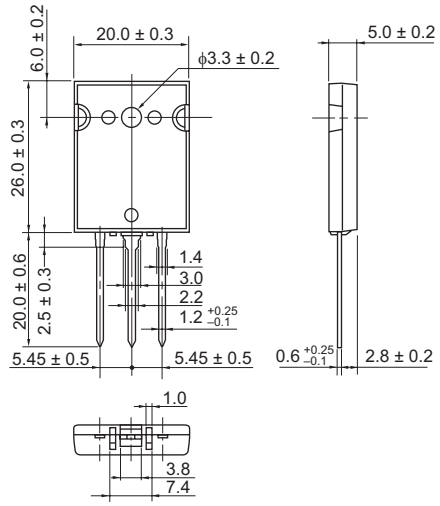
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)\ DSS}$	500	—	—	V	I_D = 10 mA, V_{GS} = 0
Gate to source leak current	I_{GSS}	—	—	±0.1	µA	V_{GS} = ±30 V, V_{DS} = 0
Zero gate voltage drain current	I_{DSS}	—	—	10	µA	V_{DS} = 500 V, V_{GS} = 0
Gate to source cutoff voltage	$V_{GS\ (off)}$	2.0	—	4.0	V	V_{DS} = 10 V, I_D = 1 mA
Static drain to source on state resistance	$R_{DS\ (on)}$	—	0.09	0.11	Ω	I_D = 25 A, V_{GS} = 10 V Note 4
Forward transfer admittance	$\|y_{fs}\|$	27	45	—	S	I_D = 25 A, V_{DS} = 10 V Note 4
Input capacitance	Ciss	—	7630	—	pF	V_{DS} = 25 V
Output capacitance	Coss	—	770	—	pF	V_{GS} = 0
Reverse transfer capacitance	Crss	—	160	—	pF	f = 1 MHz
Turn-on delay time	$t_{d\ (on)}$	—	90	—	ns	I_D = 25 A
Rise time	t_r	—	340	—	ns	V_{GS} = 10 V
Turn-off delay time	$t_{d\ (off)}$	—	370	—	ns	R_L = 10 Ω
Fall time	t_f	—	280	—	ns	Rg = 10 Ω
Total gate charge	Qg	—	220	—	nC	V_{DD} = 400 V
Gate to source charge	Qgs	—	30	—	nC	V_{GS} = 10 V
Gate to drain charge	Qgd	—	110	—	nC	I_D = 50 A
Body-drain diode forward voltage	V_{DF}	—	0.98	1.5	V	I_F = 50 A, V_{GS} = 0
Body-drain diode reverse recovery time	t_{rr}	—	190	—	ns	I_F = 50 A, V_{GS} = 0
Body-drain diode reverse recovery charge	Q_{rr}	—	1.3	—	µC	di_F/dt = 100 A/µs

Note: 4. Pulse test

Package Dimensions

JEITA Package Code	RENESAS Code	Package Name	MASS[Typ.]
—	PRSS0004ZF-A	TO-3PL / TO-3PLV	9.9g

Unit: mm



Ordering Information

Part Name	Quantity	Shipping Container
H5N5004PL-E	500 pcs	Box (Case)

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

Renesas Technology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

RENESAS SALES OFFICES

http://www.renesas.com

Refer to "**http://www.renesas.com/en/network**" for the latest and detailed information.

Renesas Technology America, Inc.
450 Holger Way, San Jose, CA 95134-1368, U.S.A
Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong
Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd.
10th Floor, No.99, Fushing North Road, Taipei, Taiwan
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology (Shanghai) Co., Ltd.
Unit2607 Ruijing Building, No.205 Maoming Road (S), Shanghai 200020, China
Tel: <86> (21) 6472-1001, Fax: <86> (21) 6415-2952

Renesas Technology Singapore Pte. Ltd.
1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd.
Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea
Tel: <82> 2-796-3115, Fax: <82> 2-796-2145

Renesas Technology Malaysia Sdn. Bhd.
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: <603> 7955-9390, Fax: <603> 7955-9510

Colophon .3.0